

L Number	Hits		DB	Time stamp
2	83926	(resistivity near (less great\$6)) (low	USPAT;	2002/08/01 15:31
		near resistance)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
3	19731	((resistivity near (less great\$6)) (low	USPAT;	2002/08/01 15:33
		near resistance)) same (substrate pad base	US-PGPUB;	
		wafer)	EPO; JPO;	
			DERWENT;	
!			IBM_TDB	
4	9517	(((resistivity near (less great\$6)) (low	USPAT;	2002/08/01 15:35
		near resistance)) same (substrate pad base	US-PGPUB;	
		wafer)) and electrode	EPO; JPO;	l i
			DERWENT;]
			IBM_TDB	
5	1230	, , , , , , , , , , , , , , , , , , , ,	USPAT;	2002/08/01 15:36
		near resistance)) same (substrate pad base	US-PGPUB;	
		wafer)) and electrode) and ((buffer near	EPO; JPO;	
		layer) GaAs)	DERWENT;	
			IBM TDB	